TECHNICAL DATA DATA SHEET 930, REV. C

ULTRA FAST RECOVERY SILICON RECTIFIER DIE

Maximum Ratings:

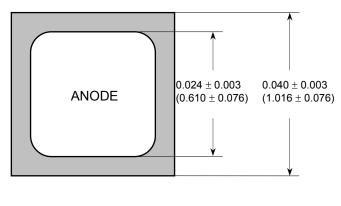
Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-		
DC Blocking Voltage	V_R		150	V
Breakdown Voltage	V_{BR}			
Max. Average Forward Current	I _{F(AV)}	@ 55°C	1.0	Α
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 ms, sine pulse (1)	35	Α
Die Size	-	-	40	mil
Max. Junction Temperature	Τ _J	-	-55 to +175	°C
Max. Storage Temperature	T _{stg}	-	-55 to +175	°C

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	1A, pulse, T _J = 25 °C	0.875	V
	V_{F2}	2.5A, pulse, T _J = 25 °C	0.975	V
	V_{F3}	1A, pulse, T _J = 100 °C	0.800	V
Max. Reverse Current	I _{R1}	$V_R = V_{RWM}$, pulse, $T_J = 25 ^{\circ}C$	1.0	μΑ
	I _{R2}	V _R = V _{RWM} , pulse, T _J = 100 °C	50	μΑ
Reverse Recovery Time	t _{rr}	$I_F = I_R = 0.5A$, $I_{RM} = 0.05A$	25	ns
Max. Junction Capacitance	C _T	V _R = 10V, T _C = 25 °C	25	pF
		$f_{SIG} = 1MHz,$		
		$V_{SIG} = 50 \text{mV (p-p)}$		

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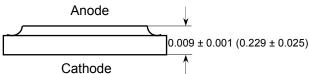
Mechanical Dimensions: In Inches (mm)



Bottom side metalization: Ti/Ni/Ag - 30 kÅ minimum.

Top side metalization: Al - 25 kÅ minimum

Bottom side is cathode, top side is anode.



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 - 221 West Industry Court ☐ Deer Park, NY 11729-4681 ☐ (631) 586-7600 FAX (631) 242-9798
 - World Wide Web Site http://www.sensitron.com E-Mail Address sales@sensitron.com •